

General Description

SRFET™ The AO4724 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent $R_{DS(ON)}$, and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

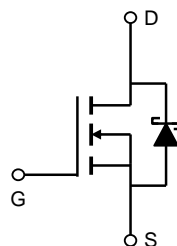
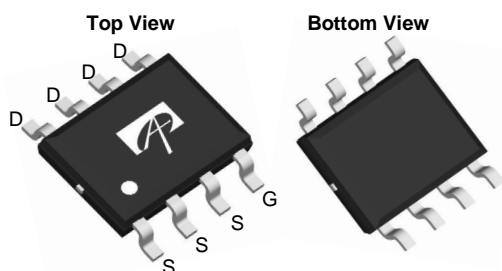
Product Summary

$V_{DS} (V) = 30V$
 $I_D = 10.5A$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 17.5m\Omega$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 29 m\Omega$ ($V_{GS} = 4.5V$)

100% UIS Tested
 100% Rg Tested



SOIC-8



SRFET™
 Soft Recovery MOSFET:
 Integrated Schottky Diode

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum		Units
		10 Sec	Steady State	
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ^{AF}	$T_A=25^\circ C$	10.5	7.7	A
	$T_A=70^\circ C$	8.5	6.2	
Pulsed Drain Current ^B	I_{DM}	80		
Power Dissipation	$T_A=25^\circ C$	3.1	1.7	W
	$T_A=70^\circ C$	2.0	1.1	
Avalanche Current ^B	I_{AR}	13		A
Repetitive avalanche energy 0.3mH ^B	E_{AR}	25		mJ
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^{AF} $t \leq 10s$	$R_{\theta JA}$	31	40	$^\circ C/W$
Maximum Junction-to-Ambient ^A Steady-State		59	75	$^\circ C/W$
Maximum Junction-to-Lead ^C Steady-State	$R_{\theta JL}$	16	24	$^\circ C/W$

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			0.1 20	mA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1.3	1.64	2	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	80			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=10.5\text{A}$ $T_J=125^\circ\text{C}$		14.4 21.5	17.5 25.8	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=8\text{A}$		22.7	29.0	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=10.5\text{A}$		23		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.4	0.5	V
I_S	Maximum Body-Diode + Schottky Continuous Current				4.8	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		696	900	pF
C_{oss}	Output Capacitance			199		pF
C_{rss}	Reverse Transfer Capacitance			81		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1.2	1.8	Ω
SWITCHING PARAMETERS						
$Q_{g(10V)}$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=10.5\text{A}$		12.4	16	nC
$Q_{g(4.5V)}$	Total Gate Charge			6.1	8	nC
Q_{gs}	Gate Source Charge			2.04		nC
Q_{gd}	Gate Drain Charge			2.7		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.43\Omega$, $R_{GEN}=3\Omega$		2.6		ns
t_r	Turn-On Rise Time			6.8		ns
$t_{D(off)}$	Turn-Off DelayTime			17		ns
t_f	Turn-Off Fall Time			3.6		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=10.5\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		20.2	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=10.5\text{A}$, $dI/dt=300\text{A}/\mu\text{s}$		7.9		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ junction to ambient thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

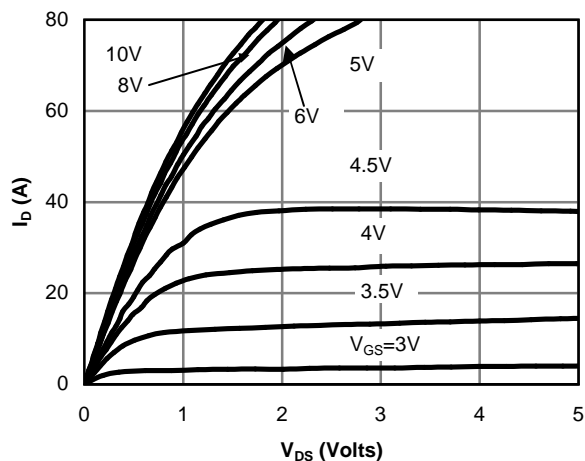


Fig 1: On-Region Characteristics

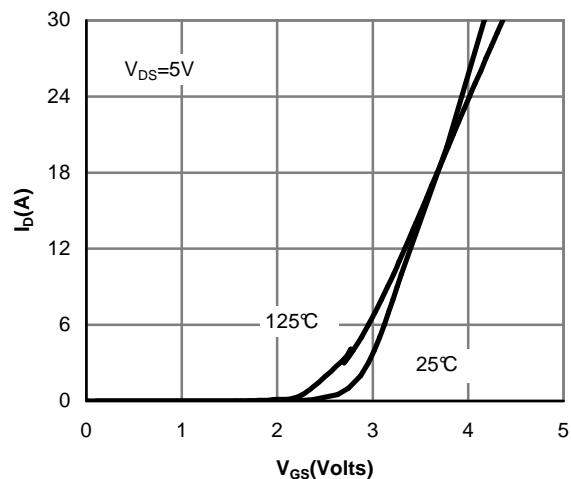


Figure 2: Transfer Characteristics

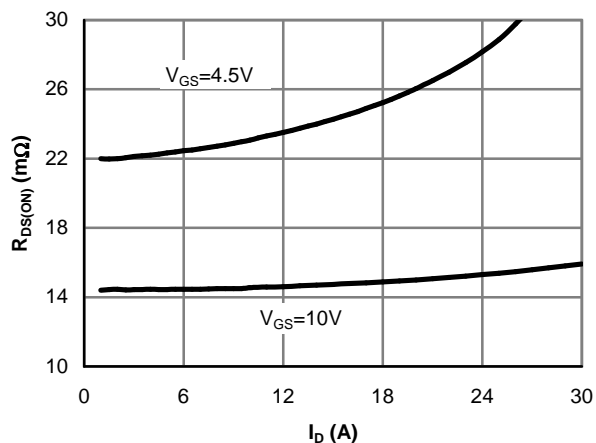


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

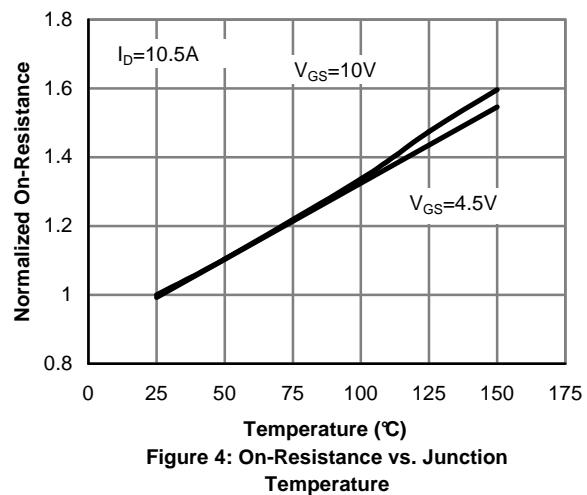


Figure 4: On-Resistance vs. Junction Temperature

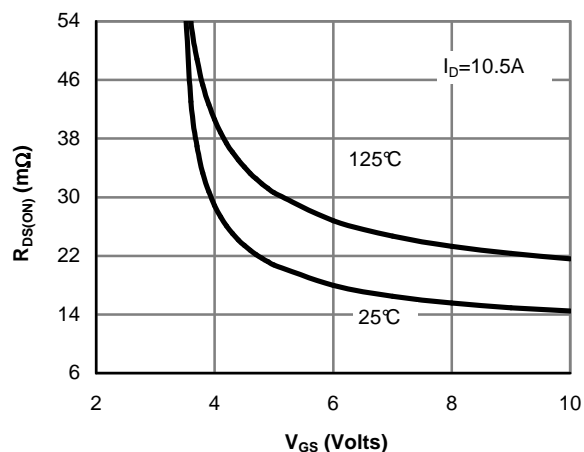


Figure 5: On-Resistance vs. Gate-Source Voltage

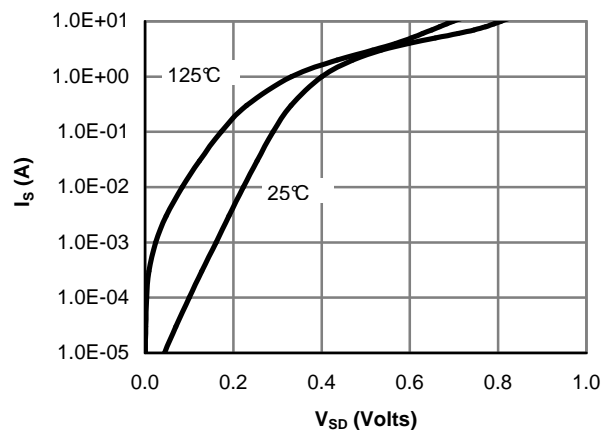


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

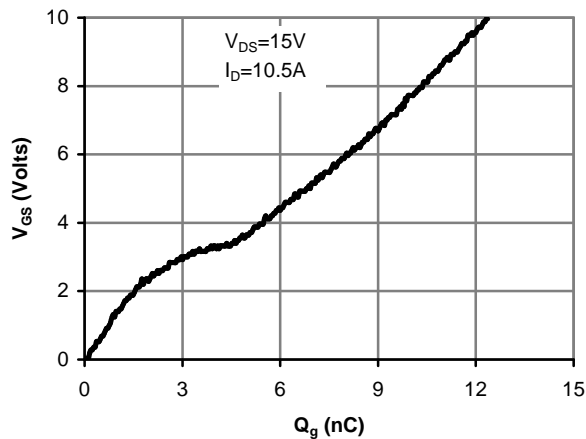


Figure 7: Gate-Charge Characteristics

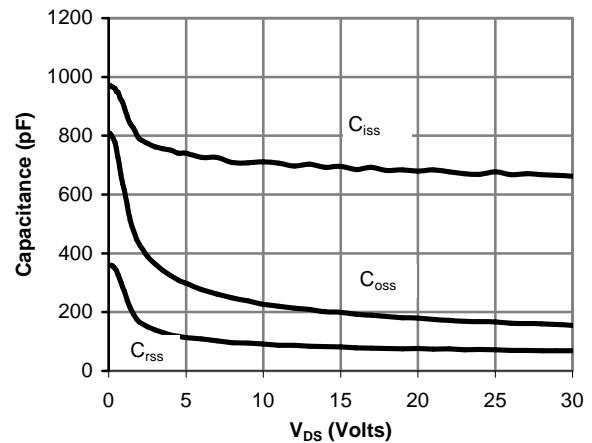


Figure 8: Capacitance Characteristics

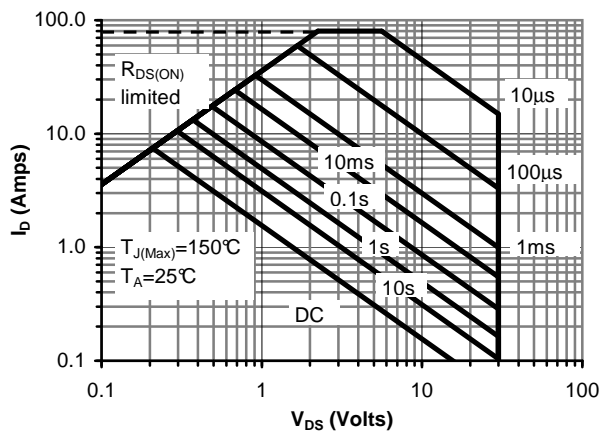


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

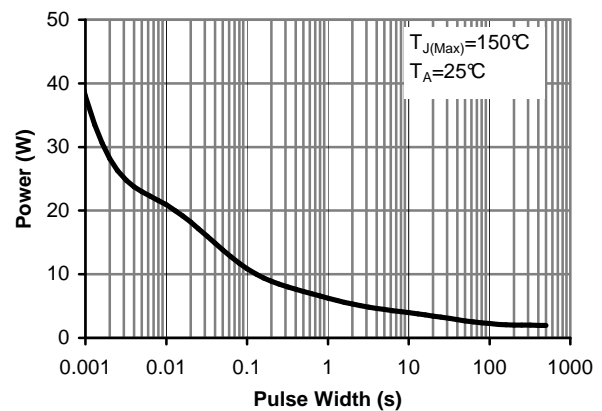


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

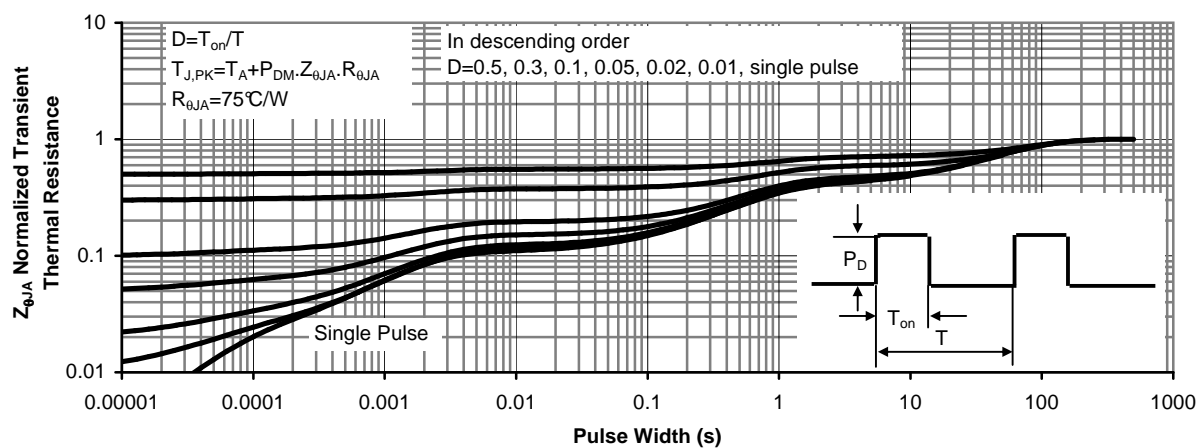


Figure 11: Normalized Maximum Transient Thermal Impedance